

$V_{RRM}$	=	<b>5500 V</b>
$I_{FAVM}$	=	<b>585 A</b>
$I_{FSM}$	=	<b>18 kA</b>
$V_{F0}$	=	<b>4.5 V</b>
$r_F$	=	<b>1.3 mΩ</b>
$V_{DClink}$	=	<b>3300 V</b>

## Fast Recovery Diode

# 5SDF 08H6005

## PRELIMINARY

Doc. No. 5SYA1116-01 Sep. 01

- Patented free-floating technology
- Industry standard housing
- Cosmic radiation withstand rating
- Low on-state and switching losses
- Optimized to use in snubberless operation

### Blocking

$V_{RRM}$	Repetitive peak reverse voltage	5500 V	Half sine wave, $t_p = 10$ ms, $f = 50$ Hz	
$I_{RRM}$	Repetitive peak reverse current	$\leq 30$ mA	$V_R = V_{RRM}, T_J = 115^\circ\text{C}$	
$V_{DClink}$	Permanent DC voltage for 100 FIT failure rate	3300 V	100% Duty	Ambient cosmic radiation at sea level in open air.
$V_{DClink}$	Permanent DC voltage for 100 FIT failure rate	3900 V	5% Duty	

### Mechanical data

$F_m$	Mounting force	min.	42 kN	
		max.	46 kN	
a	Acceleration: Device unclamped Device clamped		50 m/s <sup>2</sup>	
			200 m/s <sup>2</sup>	
m	Weight		0.83 kg	
$D_s$	Surface creepage distance	$\geq$	30 mm	
$D_a$	Air strike distance	$\geq$	20 mm	

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**On-state** (see Fig. 1, 2)

$I_{FAVM}$	Max. average on-state current	585 A	Half sine wave, $T_c = 70^\circ\text{C}$	
$I_{FRMS}$	Max. RMS on-state current	920 A		
$I_{FSM}$	Max. peak non-repetitive surge current	18 kA	$t_p = 10\text{ ms}$	Before surge: $T_c = T_j = 115^\circ\text{C}$
		40 kA	$t_p = 1\text{ ms}$	
$\int I^2 dt$	Max. surge current integral	$1.62 \cdot 10^6\text{ A}^2\text{s}$	$t_p = 10\text{ ms}$	After surge: $V_R \approx 0\text{ V}$
		$0.8 \cdot 10^6\text{ A}^2\text{s}$	$t_p = 1\text{ ms}$	
$V_F$	Forward voltage drop	$\leq 6.85\text{ V}$	$I_F = 1800\text{ A}$	$T_j = 115^\circ\text{C}$
$V_{F0}$	Threshold voltage	4.5 V	Approximation for	
$r_F$	Slope resistance	1.3 m $\Omega$	$I_F = 400 \dots 2500\text{ A}$	

**Turn-on** (see Fig. 3, 4)

$V_{fr}$	Peak forward recovery voltage	$\leq 370\text{ V}$	$di/dt = 1000\text{ A}/\mu\text{s}$ , $T_j = 115^\circ\text{C}$
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**Turn-off**

$di/dt_{crit}$	Max. decay rate of on-state current	$\leq 510\text{ A}/\mu\text{s}$	$I_F = 1800\text{ A}$ , $V_{Dclink} = 3300\text{ V}$	$T_j = 115^\circ\text{C}$
$I_{rr}$	Reverse recovery current	$\leq 900\text{ A}$		
$Q_{rr}$	Reverse recovery charge	$\leq \mu\text{C}$		
$E_{rr}$	Turn-off energy	$\leq 6.5\text{ J}$		

**Thermal**

$T_j$	Operating junction temperature range	-40...115 $^\circ\text{C}$		
$T_{stg}$	Storage temperature range	-40...125 $^\circ\text{C}$		
$R_{thJC}$	Thermal resistance junction to case	$\leq 24\text{ K/kW}$	Anode side cooled	$F_m = 42 \dots 46\text{ kN}$
		$\leq 24\text{ K/kW}$	Cathode side cooled	
		$\leq 12\text{ K/kW}$	Double side cooled	
$R_{thCH}$	Thermal resistance case to heatsink	$\leq 6\text{ K/kW}$	Single side cooled	
		$\leq 3\text{ K/kW}$	Double side cooled	

Analytical function for transient thermal impedance.

$$Z_{thJC}(t) = \sum_{i=1}^n R_i (1 - e^{-t/\tau_i})$$

i	1	2	3	4
$R_i(\text{K/kW})$	5.68	2.04	0.77	0.00
$\tau_i(\text{s})$	0.532	0.0078	0.0078	0.002
$F_m = 42 \dots 46\text{ kN}$ Double side cooled				

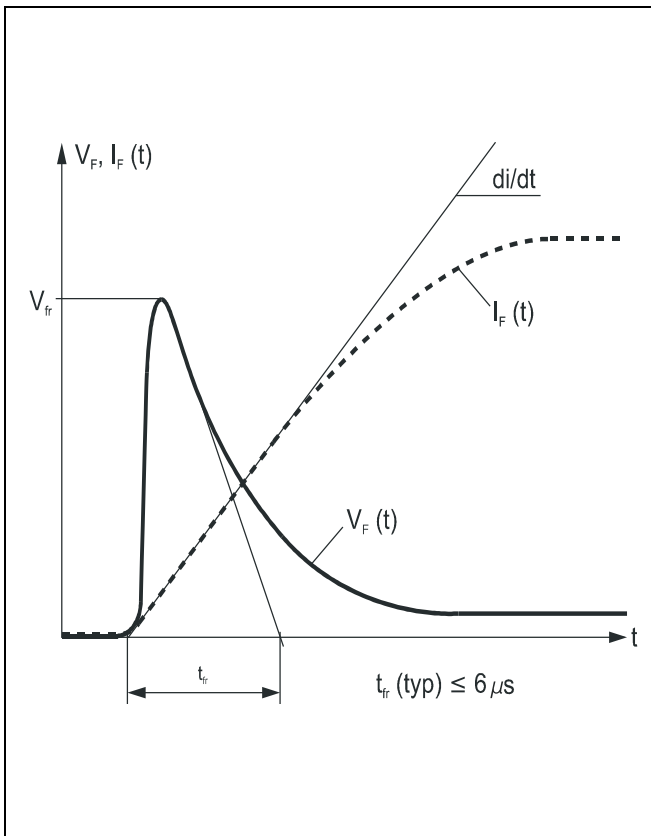


Fig. 1 Typical forward voltage waveform when the diode is turned on with high di/dt.

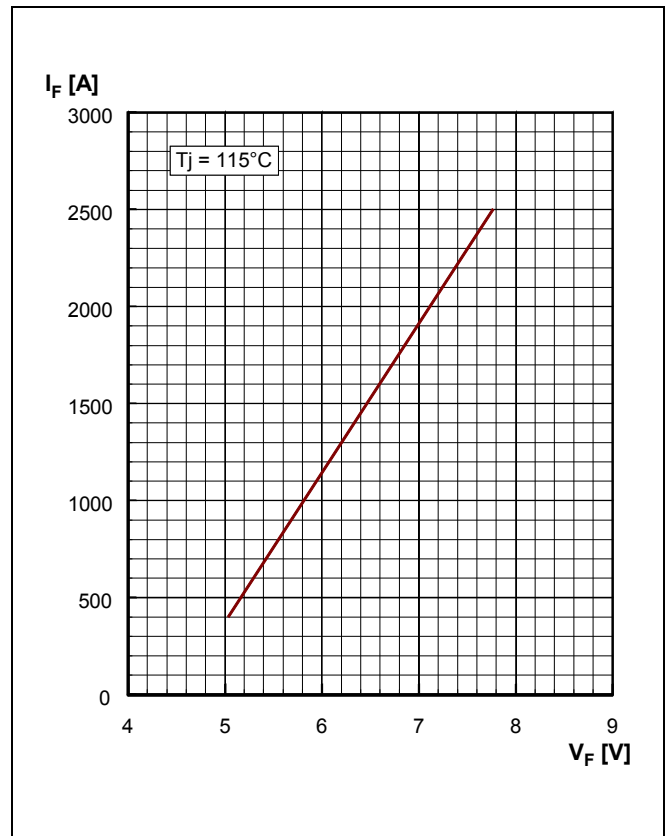


Fig. 2 Forward current vs. forward voltage.

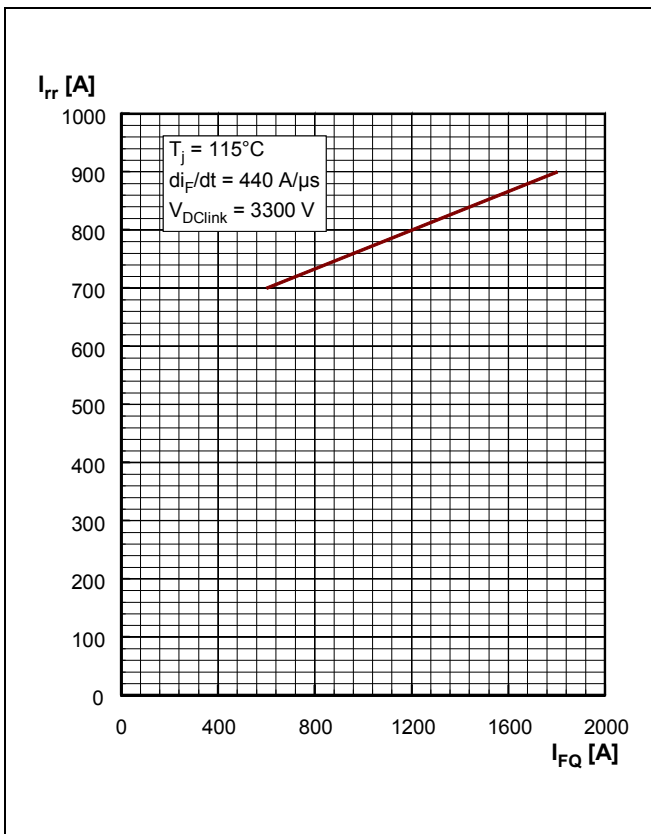


Fig. 3 Diode reverse recovery current vs. turn-off current.

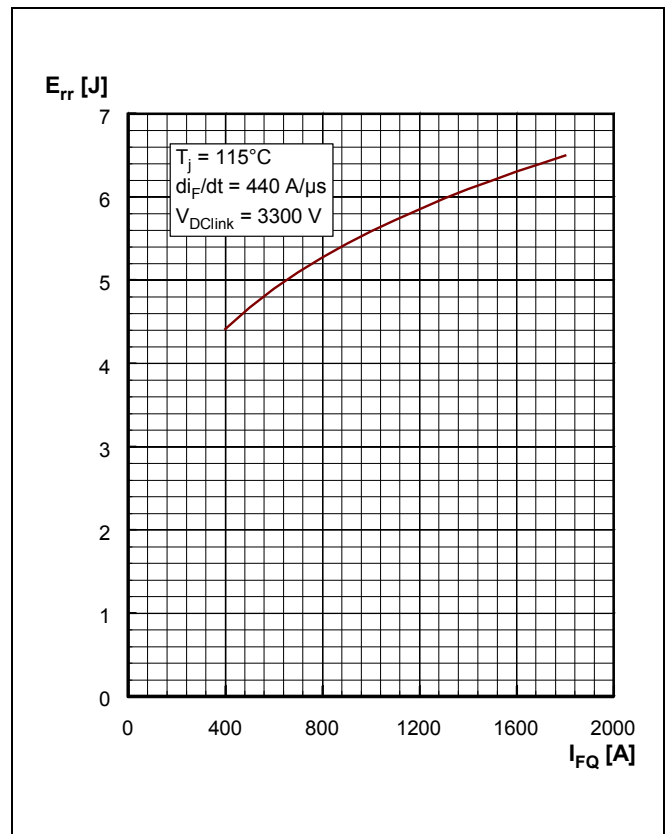


Fig. 4 Diode turn-off energy per pulse vs. turn-off current.

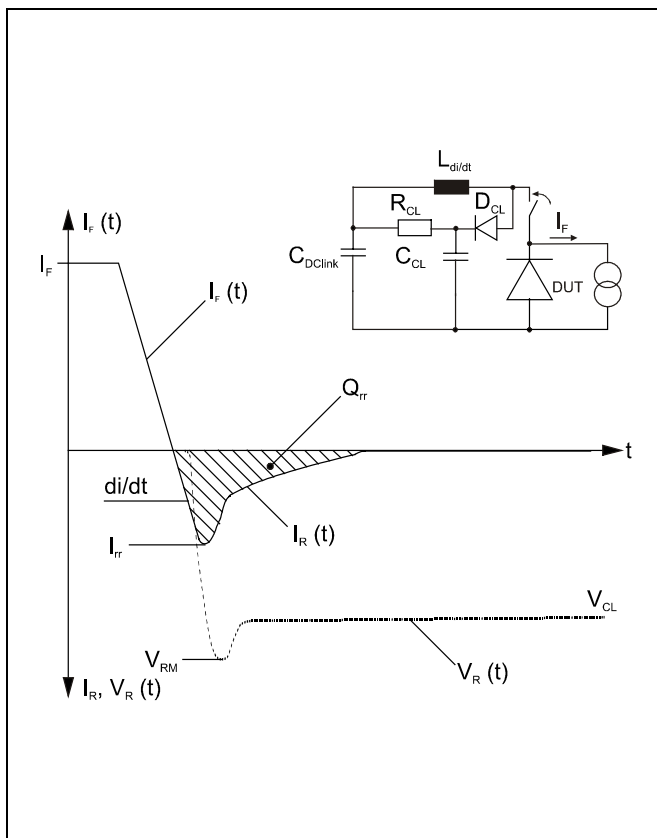


Fig. 5 Typical current and voltage waveforms at turn-off in a circuit with voltage clamp.

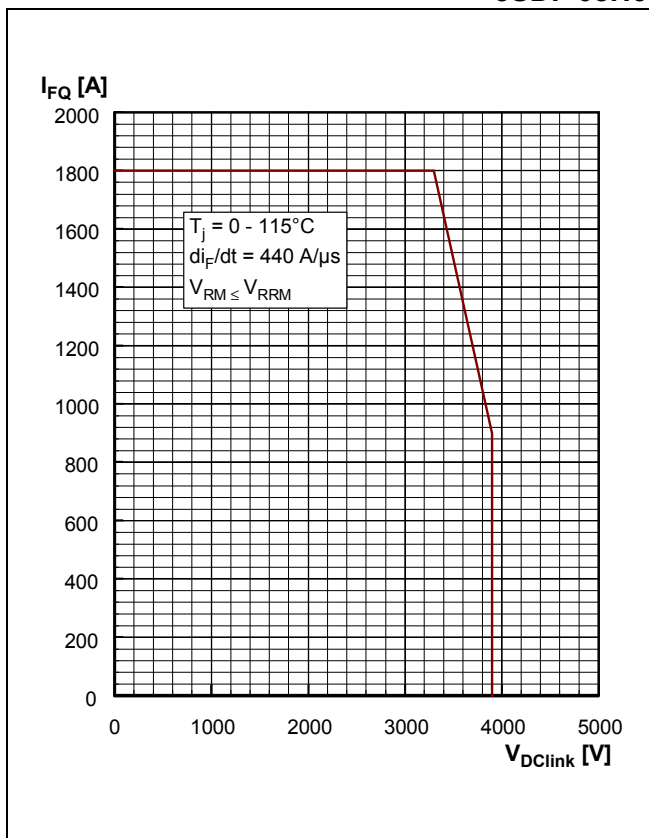
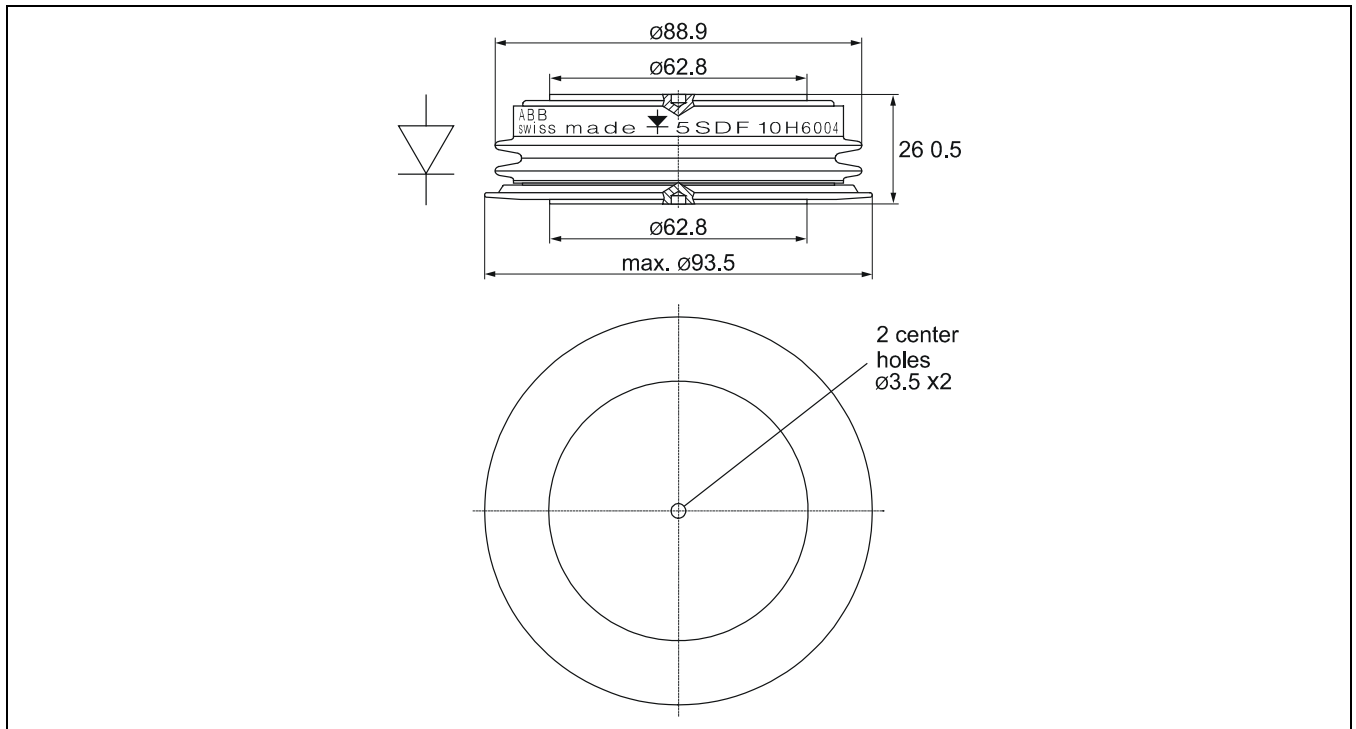


Fig. 6 Max. repetitive diode forward current.



**Fig. 7 Outline drawing. All dimensions are in millimeters and represent nominal values unless stated otherwise.**

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